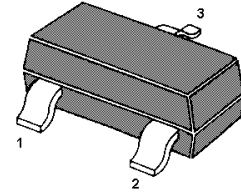
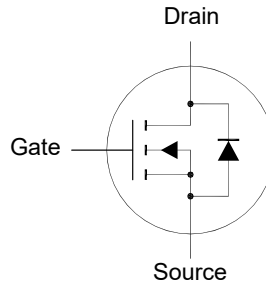


MMFTN2312-AH

N-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Surface-mounted package
- Halogen and Antimony Free(HAF), RoHS compliant



1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Applications

- Portable appliances
- Battery management

Absolute Maximum Ratings(at $T_a = 25^\circ\text{C}$ unless otherwise specified)

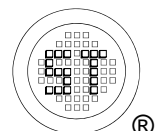
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	20	V
Drain-Gate Voltage	V_{GS}	± 8	V
Drain Current - Continuous	I_D	4.5	A
Drain Current - Pulsed ¹⁾	I_{DM}	13.5	A
Total Power Dissipation ²⁾	P_{tot}	1.25	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²⁾	$R_{\theta JA}$	100	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$.

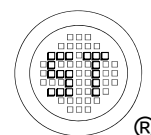
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air, $t \leq 10 \text{ s}$.



MMFTN2312-AH

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	$V_{(BR)DSS}$	20	-	-	V
Drain-Source Leakage Current at $V_{DS} = 20 \text{ V}$	I_{DSS}	-	-	1	μA
Gate-Source Leakage Current at $V_{GS} = \pm 8 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	0.5	-	1.2	V
Drain-Source On-State Resistance at $V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$ at $V_{GS} = 2.5 \text{ V}, I_D = 4.5 \text{ A}$	$R_{DS(on)}$	-	-	33 40	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 10 \text{ V}, I_D = 5 \text{ A}$	g_{fs}	-	9	-	S
Gate Resistance at $V_{GS} = 0 \text{ V}, V_{DS} = 0 \text{ V}, f = 1 \text{ MHz}$	R_g	-	2.9	-	Ω
Input Capacitance at $V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	871	-	pF
Output Capacitance at $V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	117	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	87	-	pF
Gate charge total at $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$ at $V_{DS} = 10 \text{ V}, V_{GS} = 2.5 \text{ V}, I_D = 5 \text{ A}$	Q_g	-	9.6 5.8	-	nC
Gate to Source Charge at $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$	Q_{gs}	-	2.2	-	nC
Gate to Drain Charge at $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$	Q_{gd}	-	2.3	-	nC
Turn-On Delay Time at $V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}, R_g = 3.3 \Omega$	$t_{d(on)}$	-	9	-	ns
Turn-On Rise Time at $V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}, R_g = 3.3 \Omega$	t_r	-	18	-	ns
Turn-Off Delay Time at $V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}, R_g = 3.3 \Omega$	$t_{d(off)}$	-	15	-	ns
Turn-Off Fall Time at $V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}, R_g = 3.3 \Omega$	t_f	-	2	-	ns
Body-Diode PARAMETERS					
Diode Forward Voltage at $I_s = 5 \text{ A}$	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_s	-	-	4.5	A
Body Diode Reverse Recovery Time at $I_s = 5 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	10	-	ns
Body Diode Reverse Recovery Charge at $I_s = 5 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	1.6	-	nC



Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

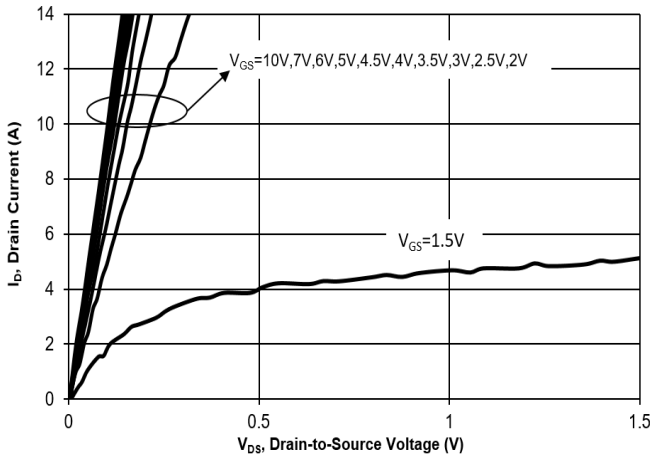


Fig. 2 Typical Transfer Characteristics

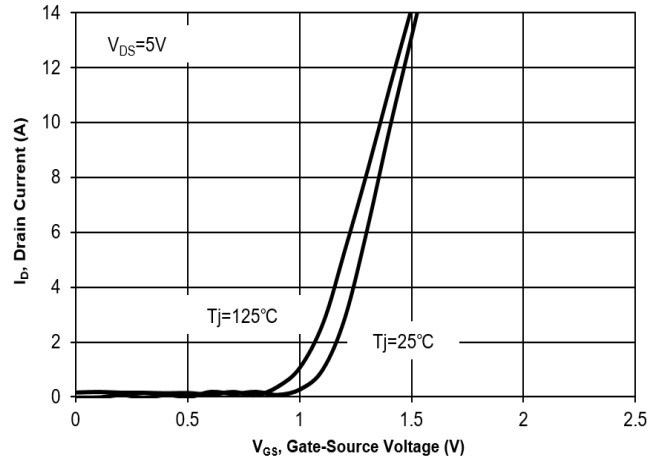


Fig. 3 On-Resistance vs. Drain Current

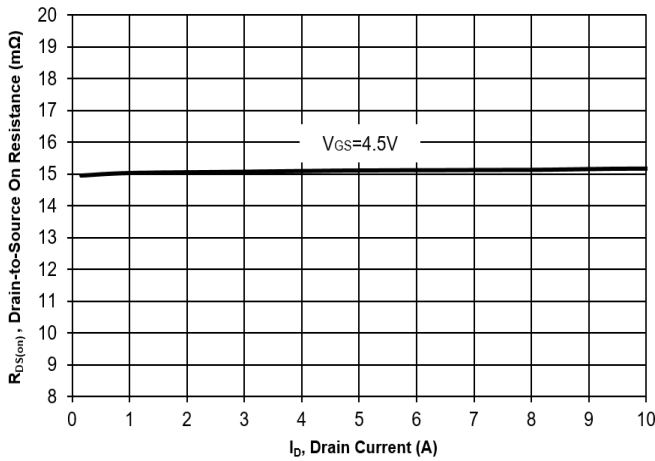


Fig. 4 On-Resistance vs. Gate to Source Voltage

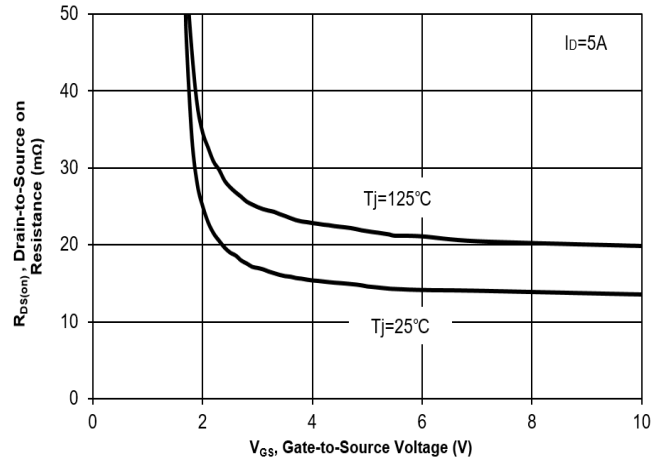


Fig. 5 On-Resistance vs. T_J

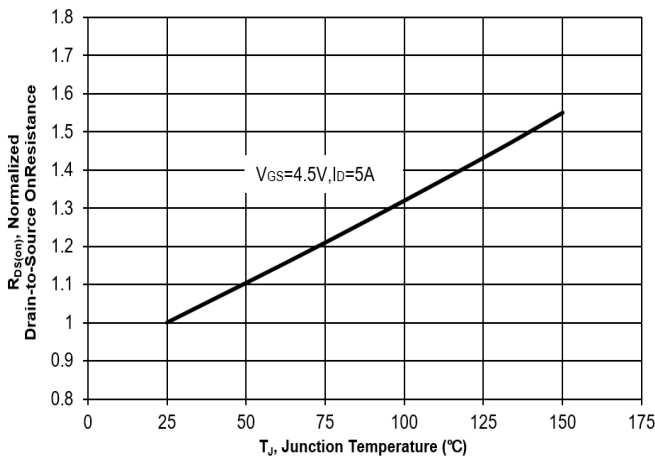
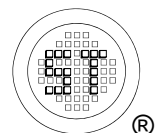
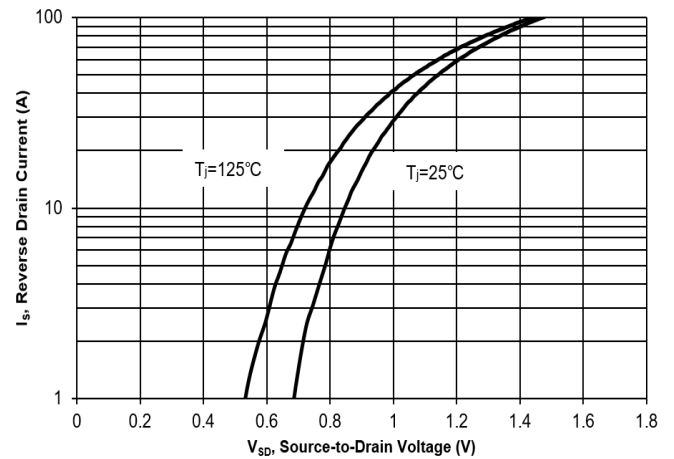


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

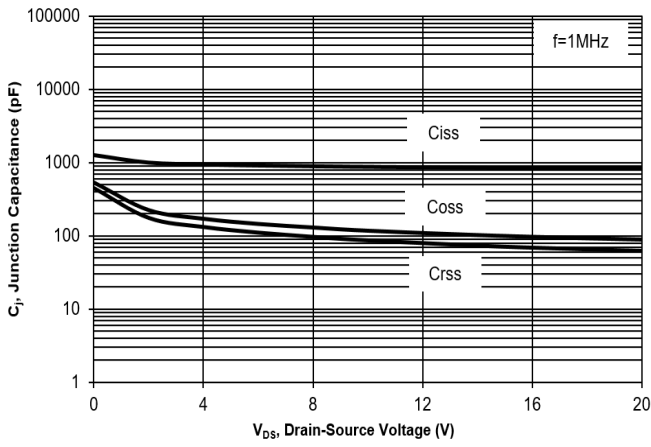


Fig. 8 Drain-Source Leakage Current vs. T_j

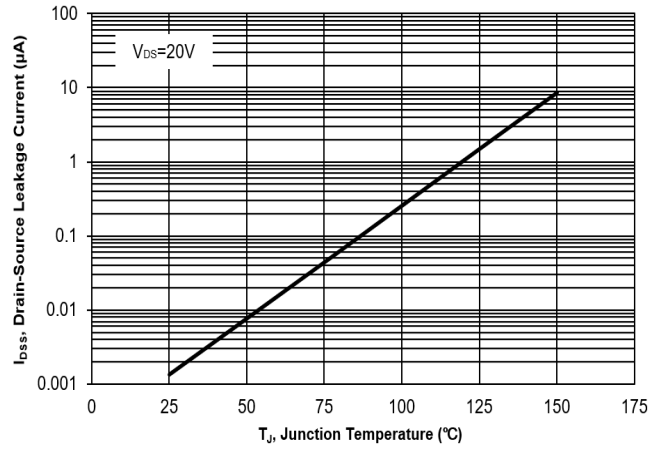


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

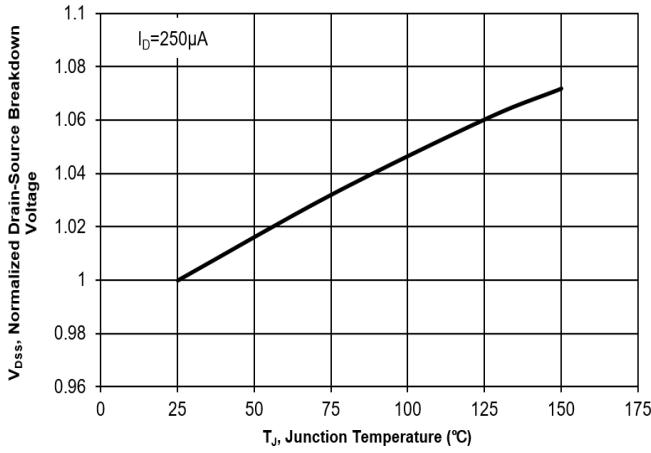


Fig. 10 Gate Threshold Variation vs. T_j

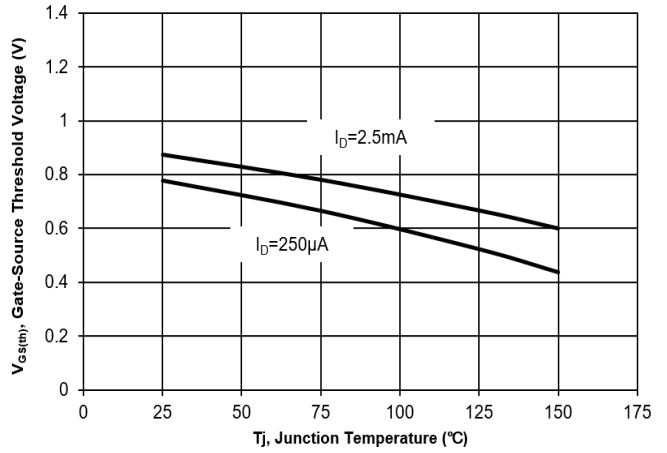
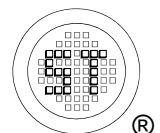
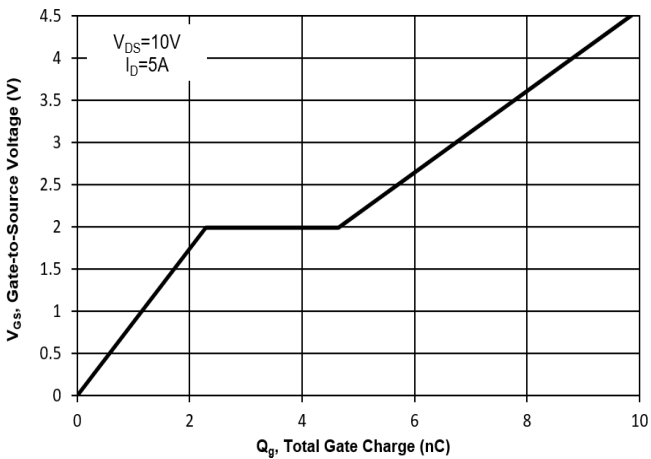


Fig. 11 Gate Charge



Test Circuits

Fig.1-1 Switching times test circuit

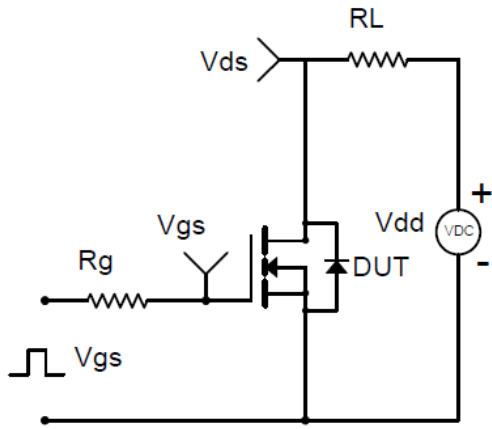


Fig.1-2 Switching Waveform

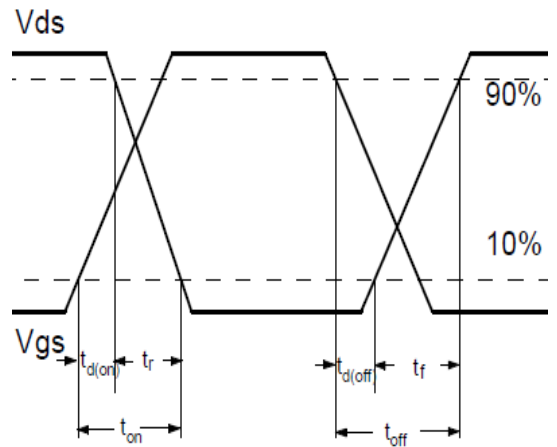


Fig.2-1 Gate charge test circuit

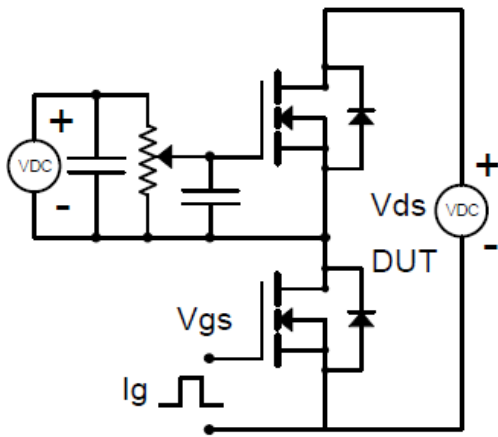
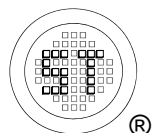
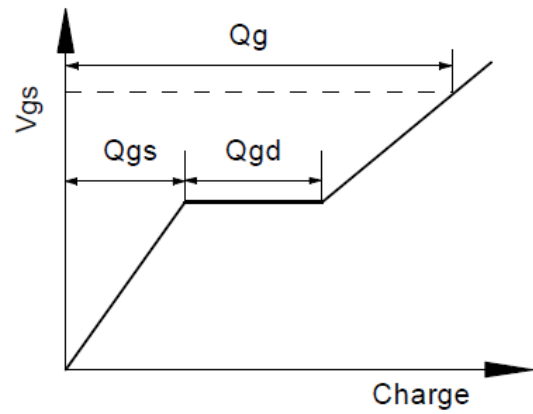


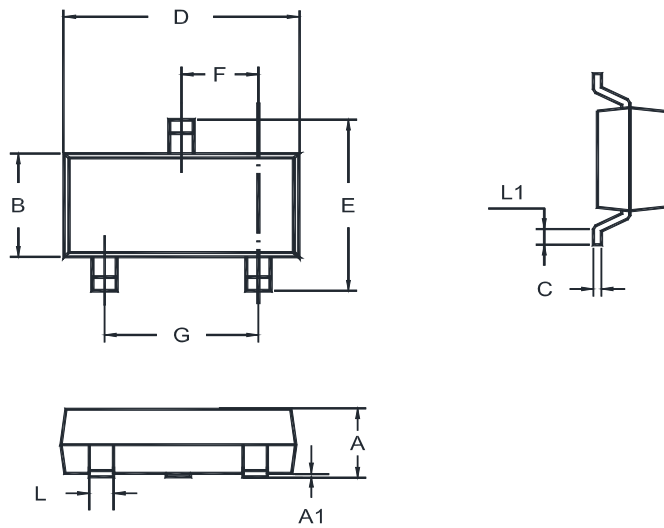
Fig.2-2 Gate charge waveform



MMFTN2312-AH

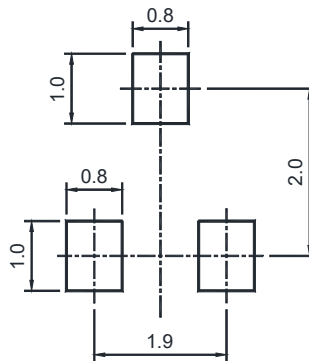
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" M23 " = Part No.

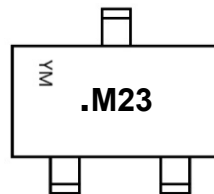
" • " = HAF (Halogen and Antimony Free)

" YM " = Date Code Marking

" Y " = Year

" M " = Month

Font type: Arial



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